

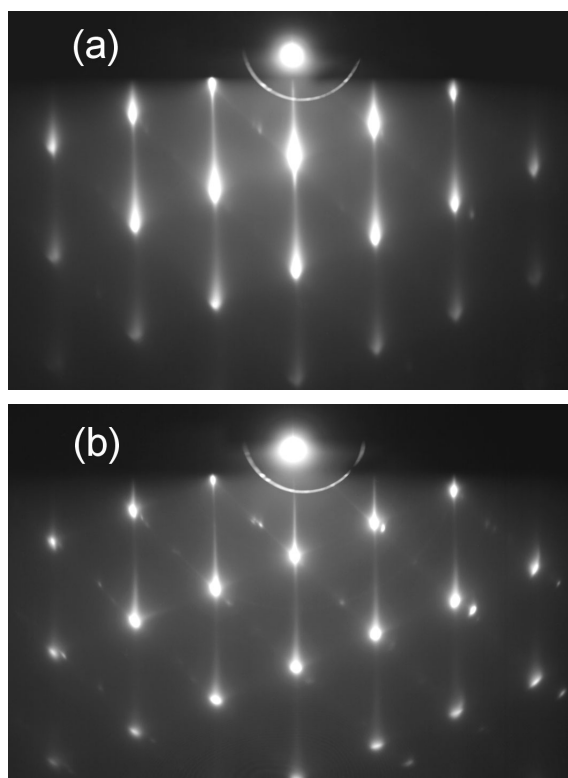
**Erratum: High-temperature atomic layer epitaxy  
of TiO<sub>2</sub> from TiCl<sub>4</sub> and H<sub>2</sub>O<sub>2</sub>-H<sub>2</sub>O  
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The publishers regret that Fig. 6 of the above article was printed incorrectly. It should be as follows:



**Fig. 6.** RHEED images for 8 nm TiO<sub>2</sub> films, ALD grown at (a) 650 and (b) 750 °C on *R*-sapphire substrates.

The Estonian Academy Publishers apologizes to the authors and our readers for this error.